

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A semiconductor device, comprising:  
a semiconductor film having a source region and a drain region;  
a gate insulating film formed on at least part of the semiconductor film; and  
a gate electrode formed on the gate insulating film,  
a sub gate electrode connected to the gate electrode, and  
a width of the gate electrode being smaller than a width of the semiconductor film,  
the gate electrode not covering any end of the semiconductor film, and  
the sub gate electrode being disposed so as to cover at least one end of the semiconductor film and so as to cover at least an entire width of the gate electrode.

2-3. (Canceled)

4. (Previously Presented) The semiconductor device according to Claim 1,  
the sub gate electrode being disposed on the gate electrode.

5-8. (Canceled)

9. (Previously Presented) A semiconductor device, comprising:  
a semiconductor film having a plurality of source regions and drain regions,  
the semiconductor film including a plurality of regions formed of an intrinsic semiconductor which is not doped with dopant;  
a gate insulating film formed on at least part of the semiconductor film; and  
a gate electrode formed on the gate insulating film;

the regions extending toward at least one of the plurality of source regions and drain regions from the gate electrode and separating adjacent source regions and adjacent drain regions.

10. (Previously Presented) The semiconductor device according to Claim 1, the semiconductor film being formed on an insulating layer.

11-16. (Canceled).

17. (Previously Presented) The semiconductor device according to Claim 1, the width of the gate electrode being smaller than the width of the semiconductor film in the direction perpendicular to the source/drain direction.

18. (Currently Amended) A semiconductor device, comprising:  
a semiconductor film having a source region and a drain region;  
a gate insulating film formed on at least part of the semiconductor film; and  
a gate electrode formed on the gate insulating film,  
a sub gate electrode connected to the gate electrode, and  
a width of the gate electrode being smaller than a width of the semiconductor film,  
  
the gate electrode not covering any end of the semiconductor film, and  
the sub gate electrode being disposed so as to cover at least one end of the semiconductor film and so as to cover at least an entire width of the gate electrode.

19. (Previously Presented) The semiconductor device according to Claim 18, the width of the gate electrode being smaller than the width of the semiconductor film in the direction perpendicular to the source/drain direction.